

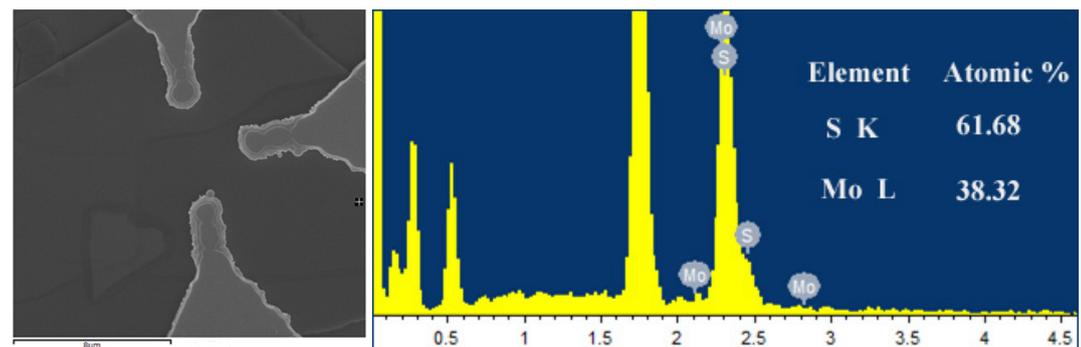
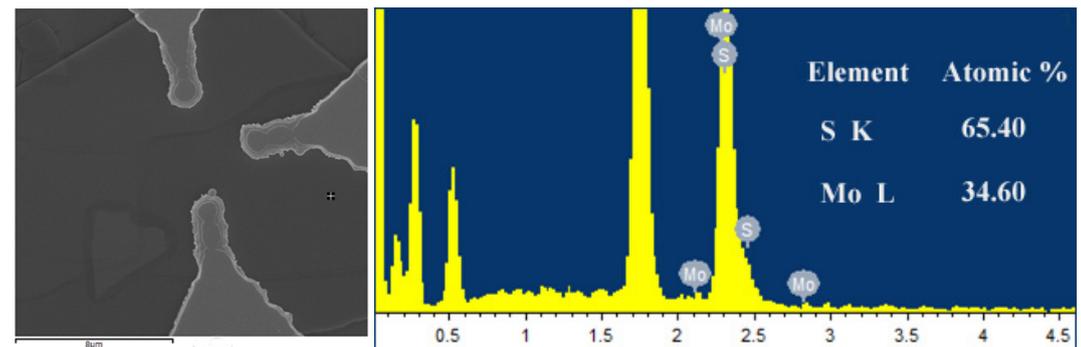
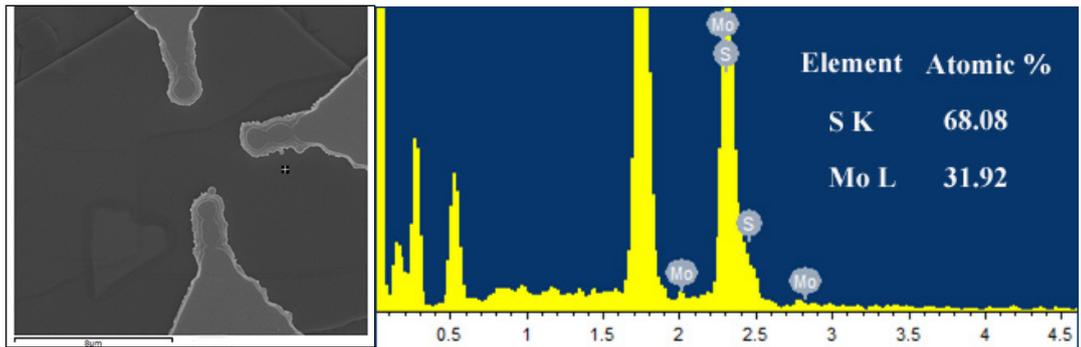
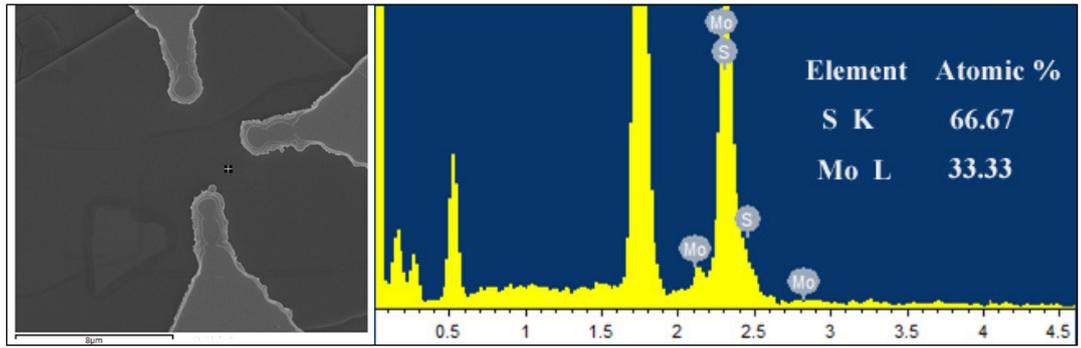
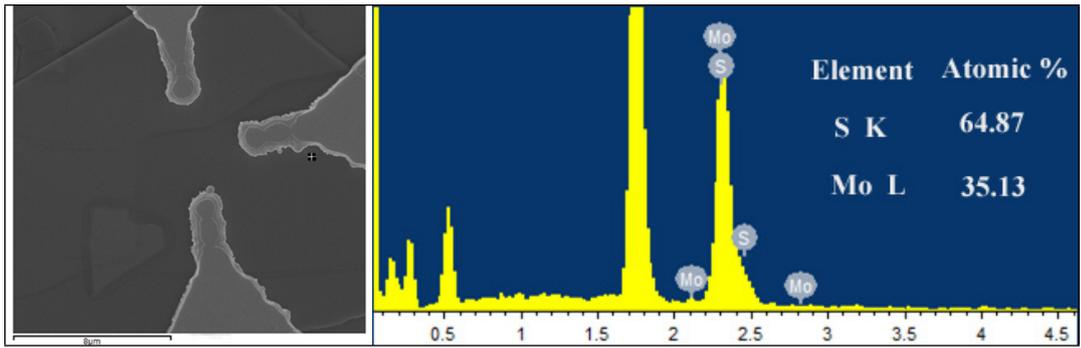
Supporting Information for

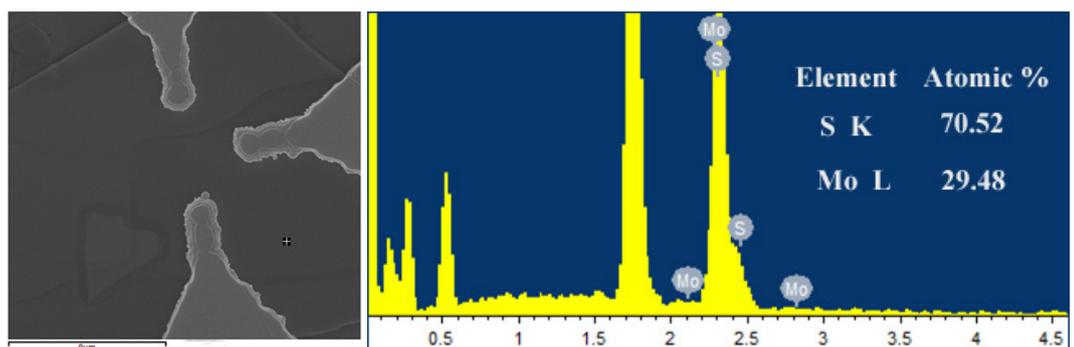
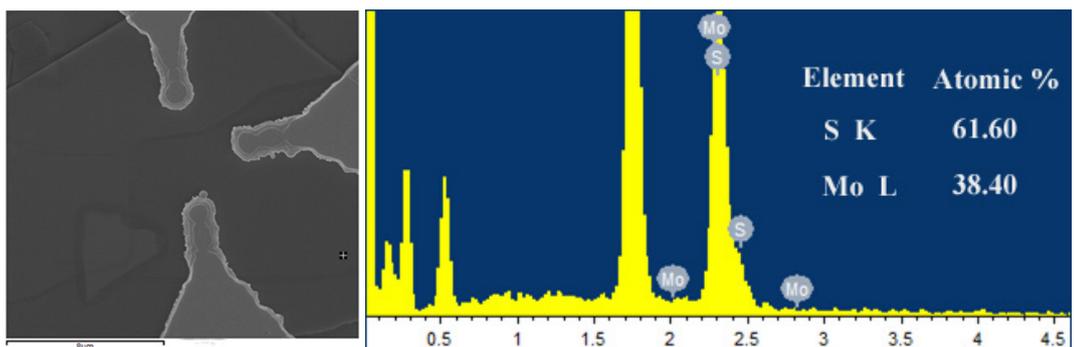
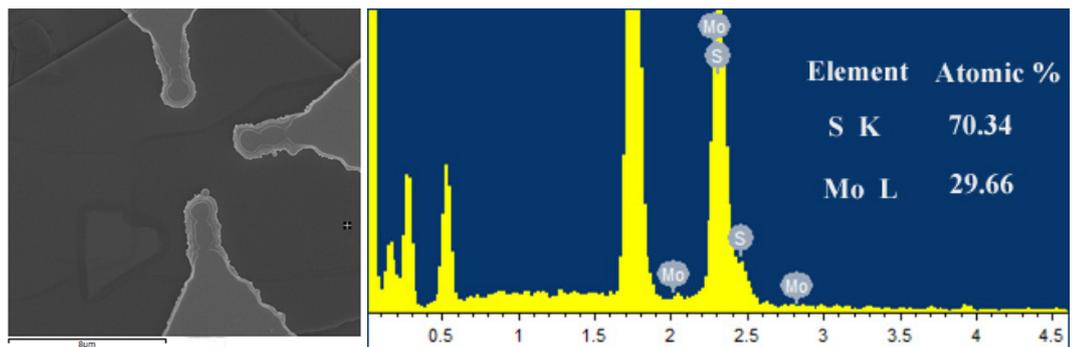
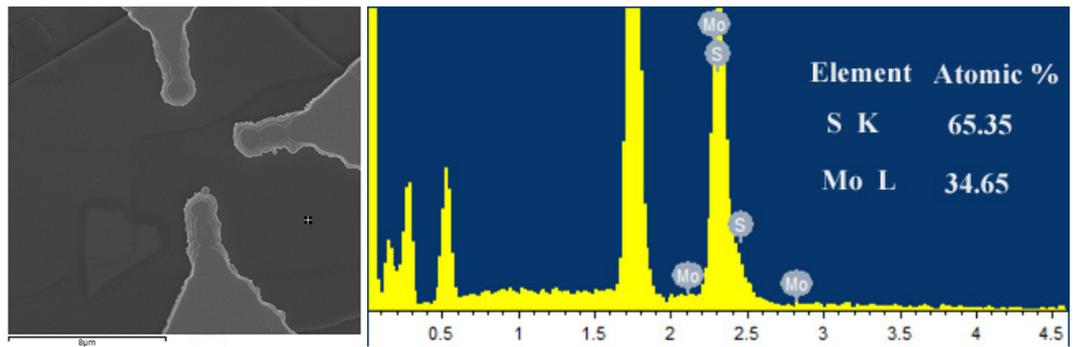
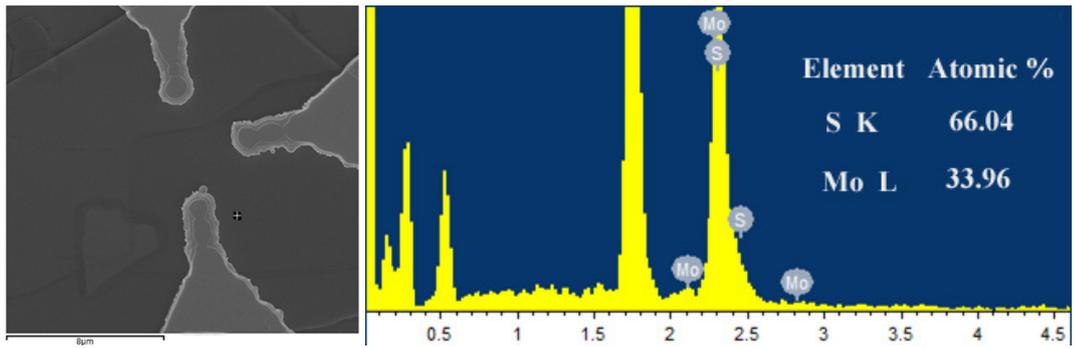
Multi-layers MoS₂ phototransistors as high performance photovoltaic cells and self-powered photodetectors

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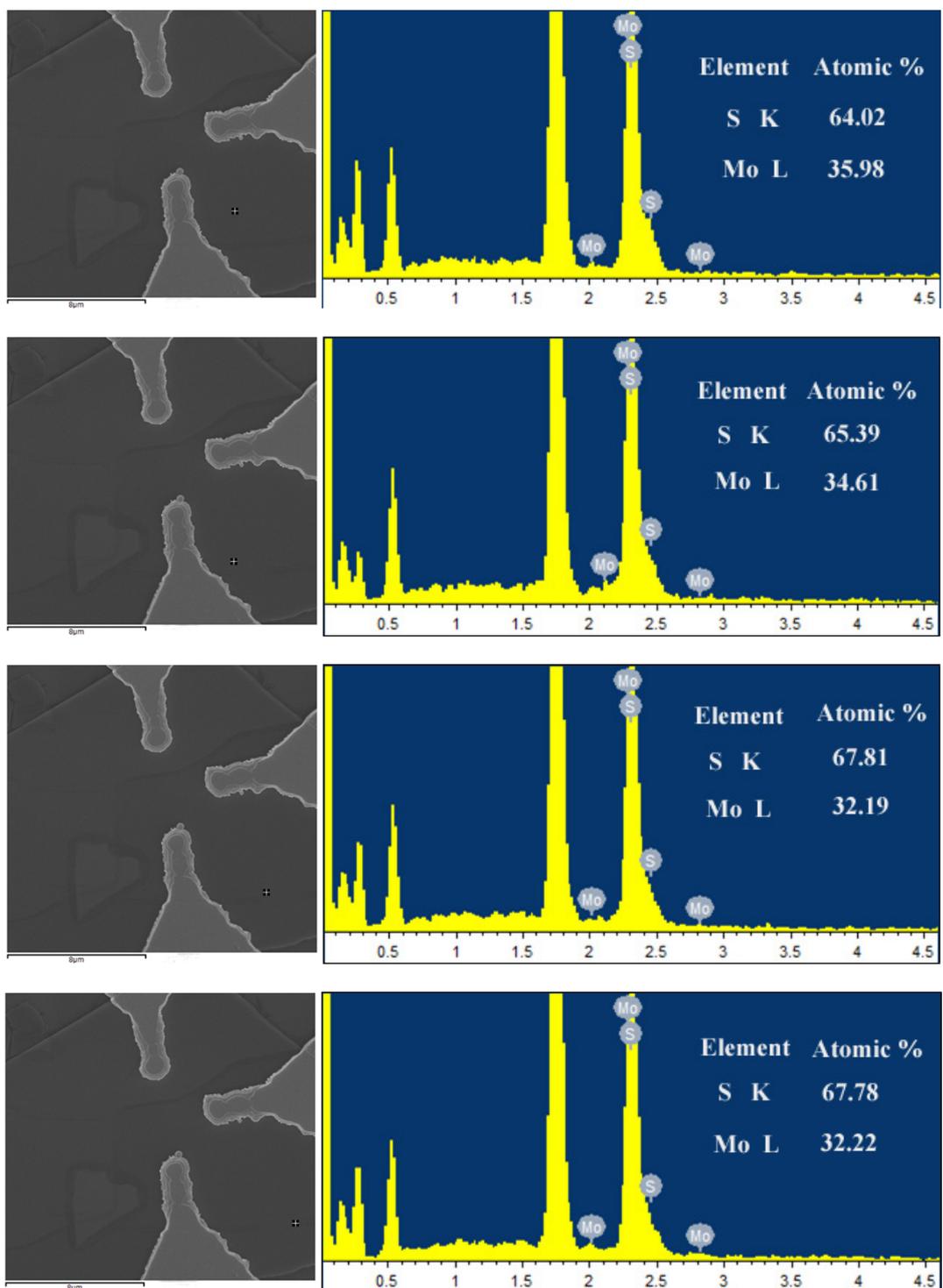


Fig. S1 EDS of multi-layer MoS₂. Left panel indicates the collection position (see the movement of mark “+”). Right panel indicates the corresponding EDS spectrum and atomic percentage.

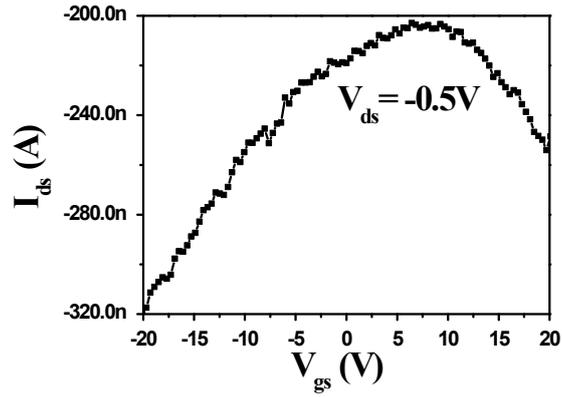


Fig. S2 The transfer curve at large negative bias voltage (-0.5V) under dark condition.

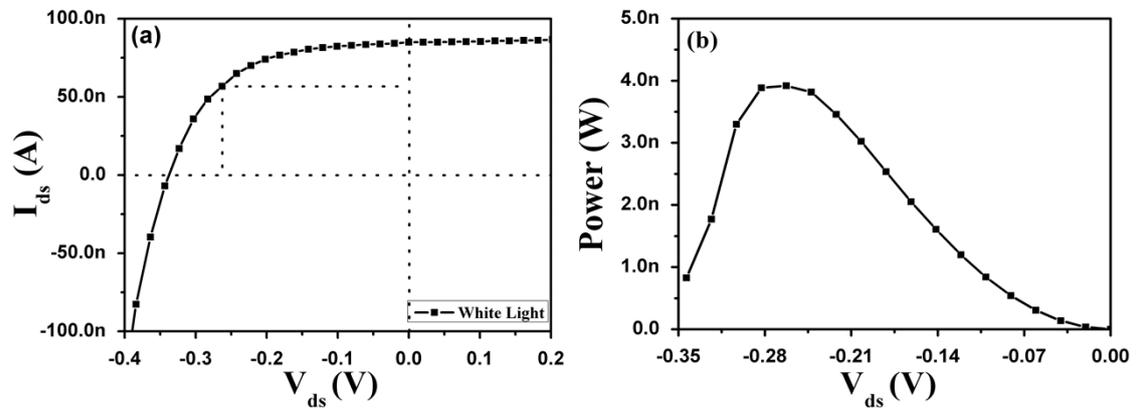


Fig. S3 (a) I_{ds} - V_{ds} of multi-layer MoS₂ device under illumination of a commercial white light LED with 1 W power. (b) Electrical power $P_{el}=I_{ds}\times V_{ds}$ as a function of V_{ds} .

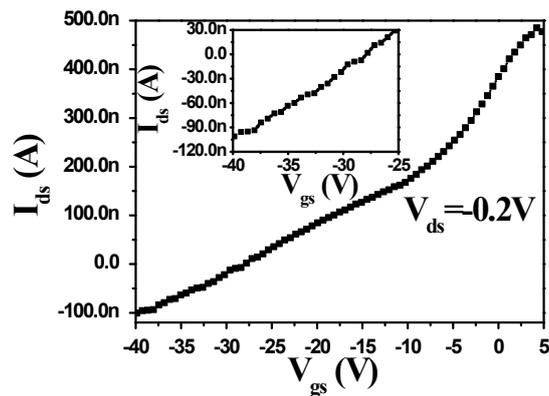


Fig. S4 The transfer curve at large negative bias voltage (-0.2V) under green illumination.

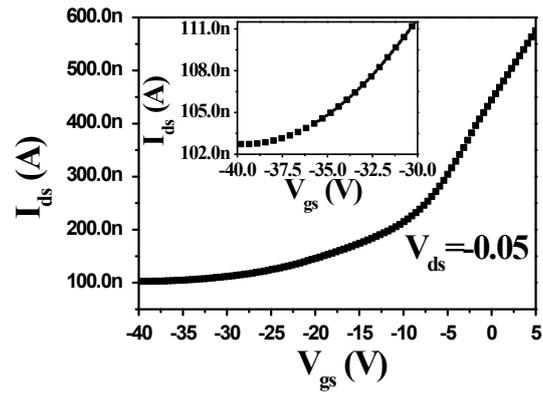


Fig. S5 The transfer curve at $V_{ds} = -0.05$ V under red illumination.